

TSV620, TSV620A, TSV621, TSV621A

Rail-to-rail input/output 29 µA 420 kHz CMOS operational amplifiers



Features

- Low supply voltage: 1.5 V–5.5 V
- Rail-to-rail input and output
- Low input offset voltage: 800 µV max (A version)
- Low power consumption: 29 µA typ
- Low power shutdown mode: 5 nA typ (TSV620)
- Gain bandwidth product: 420 kHz typ
- Unity gain stability
- Micropackages: SC70-5/6, SOT23-5/6
- Low input bias current: 1 pA typ
- Extended temperature range: -40 to 125 °C
- 4 kV HBM

Applications

- Battery-powered applications
- Portable device
- Signal conditioning
- Active filtering
- Medical instrumentation

Datasheet - production data

Description

The TSV620, TSV620A, TSV621, and TSV621A are single operational amplifiers offering low voltage, low power operation, and rail-to-rail input and output.

With a very low input bias current and low offset voltage (800 μ V maximum for the A version), the TSV62x is ideal for applications requiring precision. The device can operate at a power supply ranging from 1.5 to 5.5 V, and therefore suit battery-powered devices and extend their battery life.

This product features an excellent speed/power consumption ratio, offering a 420 kHz gain bandwidth while consuming only 29 μ A at a 5 V supply voltage.

These operational amplifiers are unity gain stable for capacitive loads up to 100 pF.

The device is internally adjusted to provide very narrow dispersion of AC and DC parameters, especially power consumption, product gain bandwidth, and slew rate.

The TSV62x present high tolerance to ESD, sustaining 4 kV for the human body model.

The device is offered in macropackages, SC70-6 and SOT23-6 for the TSV620 and SC70-5 and SOT23-5 for the TSV621. They are guaranteed for industrial temperature ranges from -40 $^{\circ}$ C to 125 $^{\circ}$ C.

All these features make the TSV620, TSV620A, TSV621, and TSV621A ideal for sensor interfaces, battery-supplied and portable applications, as well as active filtering.

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This is information on a product in full production.

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Absolute maximum ratings and operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage ⁽¹⁾	6	
V _{id}	Differential input voltage ⁽²⁾	±V _{CC}	V
V _{in}	Input voltage ⁽³⁾	$(V_{CC-}) - 0.2$ to $(V_{CC+}) + 0.2$	
l _{in}	Input current ⁽⁴⁾	10	mA
SHDN	Shutdown voltage ⁽⁵⁾	$(V_{CC-}) - 0.2$ to $(V_{CC+}) + 0.2$	V
T _{stg}	Storage temperature	-65 to 150	°C
R _{thja}	Thermal resistance junction to ambient ^{(6) (7)} SC70-5 SOT23-5 SOT23-6 SC70-6	205 250 240 232	°C/W
Тj	Maximum junction temperature	150	°C
	HBM: human body model ⁽⁸⁾	4	kV
ESD	MM: machine model ⁽⁹⁾	300	V
	CDM: charged device model ⁽¹⁰⁾	1.5	kV
	Latch-up immunity	200	mA

Table 1. Absolute maximum ratings (AMR)

1. All voltage values, except differential voltage are with respect to network ground terminal.

- 2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
- 3. Vcc-Vin must not exceed 6 V.
- 4. Input current must be limited by a resistor in series with the inputs.
- 5. Vcc-SHDN must not exceed 6 V.
- 6. Short-circuits can cause excessive heating and destructive dissipation.
- 7. R_{th} are typical values.
- 8. Human body model: 100 pF discharged through a 1.5 k Ω resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
- 9. Machine mode: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω), done for all couples of pin combinations with other pins floating.
- 10. Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to the ground.

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage	1.5 to 5.5	V
V _{icm}	Common mode input voltage range	(V _{CC-}) - 0.1 to (V _{CC+}) + 0.1	v
T _{oper}	Operating free air temperature range	-40 to +125	°C

Table 2. Operating conditions



2 Electrical characteristics

Table 3. Electrical characteristics at $V_{CC+} = 1.8$ V with $V_{DD} = 0$ V, $V_{icm} = V_{CC}/2$, $T_{op} = 25$ °C, and R_L connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perfo	rmance		•			
		TSV62x TSV62xA			4 0.8	
V _{io}	Offset voltage	T _{min} < T _{op} < T _{max} TSV62x TSV62xA			6 2.8	mV
$\Delta V_{io}/\Delta T$	Input offset voltage drift			2		µV/°C
	Input offset current			1	10 ⁽¹⁾	
l _{io}	$(V_{out} = V_{CC}/2)$	$T_{min} < T_{op} < T_{max}$		1	100	- 0
	Input bias current			1	10 ⁽¹⁾	рА
l _{ib}	$(V_{out} = V_{CC}/2)$	$T_{min} < T_{op} < T_{max}$		1	100	
CMR	Common mode rejection ratio	0 V to 1.8 V, V _{out} = 0.9 V	53	74		
CIVIR	20 log ($\Delta V_{ic}/\Delta V_{io}$)	$T_{min} < T_{op} < T_{max}$	51			dD
٨	orgo olgool voltago goin	R_L = 10 k Ω V _{out} = 0.5 V to 1.3 V	78	95		dB
A _{vd}	Large signal voltage gain	$T_{min} < T_{op} < T_{max}$	73			
M	High level output voltage (V _{OH} = V _{CC} - V _{out})	R _L = 10 kΩ		5	35	
V _{OH}		$T_{min} < T_{op} < T_{max}$			50	mV
V	Low level output voltage	$R_L = 10 \ k\Omega$		4	35	1110
V _{OL}		$T_{min} < T_{op} < T_{max}$			50	
	lsink	V _o = 1.8 V	6	12		
Ι.		$T_{min} < T_{op} < T_{max}$	4			mA
I _{out}	Isource	$V_0 = 0 V$	6	10		
		$T_{min} < T_{op} < T_{max}$	4			
I _{CC}	Supply current (per operator)	No load, $V_{out} = V_{CC}/2$		25	31	μA
-00		$T_{min} < T_{op} < T_{max}$			33	μ.,
AC perfo	rmance					
GBP	Gain bandwidth product	R_L = 10 kΩ, C_L = 100 pF, f = 100 kHz	275	340		kHz
Fu	Unity gain frequency			280		
φm	Phase margin	R _L = 10 kΩ, C _L = 100 pF		45		Degrees
G _m	Gain margin			9		dB
SR	Slew rate	R _L = 10 kΩ, C _L = 100 pF, Av = 1	0.084	0.11	0.14	V/µs

1. Guaranteed by design.



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit			
DC perfo	DC performance								
		SHDN = V _{CC-}		2.5	50	nA			
I _{CC}	Supply current in shutdown mode (all operators)	T _{min} < T _{op} < 85° C			200	ΠA			
		T _{min} < T _{op} < 125° C			1.5	μA			
t _{on}	Amplifier turn-on time	$R_L = 2 k\Omega$ $V_{out} = (V_{CC})$ to $V_{CC} + 0.2$		300		20			
t _{off}	Amplifier turn-off time	$R_L = 2 k\Omega$ $V_{out} = (V_{CC+}) - 0.5 \text{ to } (V_{CC+}) + 0.7$		30		ns			
V _{IH}	SHDN logic high		1.3			V			
V _{IL}	SHDN logic low				0.5	v			
I _{IH}	SHDN current high	SHDN = V _{CC+}		10					
Ι _{ΙL}	SHDN current low	SHDN = V _{CC-}		10		pА			
	Output leakage in shutdown	SHDN = V _{CC-}		50					
I _{OLeak}	mode	T _{min} < T _{op} < 125 °C		1		nA			

Table 4. Shutdown characteristics V_{CC} = 1.8 V



Table 5. V_{CC+} = 3.3 V, V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T_{op} = 25° C, R_L connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
DC perfo	rmance					
		TSV62x TSV62xA			4 0.8	
V _{io}	Offset voltage	T _{min} < T _{op} < T _{max} TSV62x TSV62xA			6 2.8	mV
$\Delta V_{io}/\Delta T$	Input offset voltage drift			2		µV/°C
	Input offect ourrent			1	10 ⁽¹⁾	
l _{io}	Input offset current	$T_{min} < T_{op} < T_{max}$		1	100	~^
1	Input biog ourrent			1	10 ⁽¹⁾	pА
l _{ib}	Input bias current	$T_{min} < T_{op} < T_{max}$		1	100	
CMR	Common mode rejection ratio	0 V to 3.3 V, V _{out} = 1.75 V	57	79		
CIVIR	20 log ($\Delta V_{ic}/\Delta V_{io}$)	$T_{min} < T_{op} < T_{max}$	53			dB
٨	Large signal veltage gain	R_L =10 k Ω , V_{out} = 0.5 V to 2.8 V	81	98		uв
A _{vd}	Large signal voltage gain	$T_{min} < T_{op} < T_{max}$	76			
M	High level output voltage (V _{OH} = V _{CC} - V _{out})	R _L = 10 kΩ		5	35	
V _{OH}		$T_{min} < T_{op} < T_{max}$			50	mV
M	Low level output voltage	R _L = 10 kΩ		4	35	ΠV
V _{OL}		$T_{min} < T_{op} < T_{max}$			50	
	lsink	$V_0 = 5 V$	30	45		
Ι.		$T_{min} < T_{op} < T_{max}$	25			mA
I _{out}	Isource	$V_0 = 0 V$	30	38		
		$T_{min} < T_{op} < T_{max}$	25			
laa	Supply current (per operator)	No load, V _{out} = 2.5 V		26	33	μA
I _{CC}		$T_{min} < T_{op} < T_{max}$			35	μΑ
AC perfo	rmance					
GBP	Gain bandwidth product	R_L = 10 kΩ, C_L = 100 pF, f = 100 kHz	310	380		kHz
Fu	Unity gain frequency			310]
φm	Phase margin	R _L = 10 kΩ, C _L = 100 pF		45		Degrees
G _m	Gain margin			9		dB
SR	Slew rate	$R_L = 10 \text{ k}\Omega, C_L = 100 \text{ pF}, A_V = 1$	0.094	0.12		V/µs

1. Guaranteed by design.



Table 6. V_{CC+} = 5 V, V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T_{op} = 25° C, R_L connected to $V_{CC}/2$
(unless otherwise specified)

Symbol	Parameter		Min.	Тур.	Max.	Unit
DC perfo	rmance					
		TSV62x TSV62xA			4 0.8	
V _{io}	Offset voltage	T _{min} < T _{op} < T _{max} TSV62x TSV62xA			6 2.8	mV
$\Delta V_{io}/\Delta T$	Input offset voltage drift			2		µV/°C
				1	10 ⁽¹⁾	
I _{io}	Input offset current	T _{min} < T _{op} < T _{max}		1	100	
				1	10 ⁽¹⁾	рА
I _{ib}	Input bias current	T _{min} < T _{op} < T _{max}		1	100	
CMR	Common mode rejection ratio	0 V to 5 V, V _{out} = 2.5 V	60	80		
CIVIN	20 log ($\Delta V_{ic}/\Delta V_{io}$)	$T_{min} < T_{op} < T_{max}$	55			
SVR	Supply voltage rejection ratio 20	V _{CC} = 1.8 to 5 V	75	102		dB
SVK	$\log \left(\Delta V_{CC} / \Delta V_{io} \right)$	$T_{min} < T_{op} < T_{max}$	73			uв
٨	Large signal voltage gain	R _L =10 kΩ, V _{out} = 0.5 V to 4.5 V	85	98		
A _{vd}		T _{min} < T _{op} < T _{max}	80			
V	High level output voltage (V _{OH} = V _{CC} - V _{out})	R _L = 10 kΩ		7	35	
V _{OH}		$T_{min} < T_{op} < T_{max}$			50	mV
M		R _L = 10 kΩ		6	35	IIIV
V _{OL}	Low level output voltage	$T_{min} < T_{op} < T_{max}$			50	
	1	$V_0 = 5 V$	40	69		
	lsink	T _{min} < T _{op} < T _{max}	35	65		
l _{out}	1	$V_0 = 0 V$	40	74		mA
	Isource	T _{min} < T _{op} < T _{max}	35	68		
	Current (nor energies)	No load, V _{out} = 2.5 V		29	36	
I _{CC}	Supply current (per operator)	$T_{min} < T_{op} < T_{max}$			38	μA
AC perfo	rmance					
GBP	Gain bandwidth product	R_{L} = 10 kΩ C _L = 100 pF, f = 100 kHz	350	420		kHz
Fu	Unity gain frequency			360		
φm	Phase margin	R _L = 10 kΩ, C _L = 100 pF		45		Degrees
G _m	Gain margin			9		dB
SR	Slew rate	R _L = 10 kΩ, C _L = 100 pF, A _V = 1	0.108	0.14		V/µs



Table 6. V_{CC+} = 5 V, V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T_{op} = 25° C, R_L connected to $V_{CC}/2$ (unless otherwise specified) (continued)

Symbol	Parameter		Min.	Тур.	Max.	Unit
e _n	Equivalent input noise voltage	f = 1 kHz		70		$\frac{nV}{\sqrt{Hz}}$
THD	Total harmonic distortion			0.004		%

1. Guaranteed by design.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit			
DC perform	DC performance								
		SHDN = V _{CC-}		5	50	nA			
I _{CC}	Supply current in shutdown mode (all operators)	T _{min} < T _{op} < 85 °C			200	ΠA			
	···· (· ·····)	T _{min} < T _{op} < 125 °C			1.5	μA			
t _{on}	Amplifier turn-on time	$R_L = 2 k\Omega, V_{out} = (V_{CC-}) to (V_{CC-})$ + 0.2		300		20			
t _{off}	Amplifier turn-off time	$R_L = 2 k\Omega V_{out} = (V_{CC+}) - 0.5 to$ (V _{CC+}) + 0.7		30		ns			
V _{IH}	SHDN logic high		4.5			V			
V _{IL}	SHDN logic low				0.5	v			
I _{IH}	SHDN current high	SHDN = V _{CC+}		10					
I _{IL}	SHDN current low	SHDN = V _{CC-}		10		pА			
	Output leakage in shutdown	SHDN = V _{CC-}		50					
l _{OLeak}	mode	T _{min} < T _{op} < 125 °C		1		nA			

Table 7. Shutdown characteristics $V_{CC} = 5 V$



















3 Application information

3.1 Operating voltages

The TSV620, TSV620A, TSV621, and TSV621A can operate from 1.5 to 5.5 V. Their parameters are fully specified for 1.8, 3.3, and 5 V power supplies. However, the parameters are very stable in the full V_{CC} range and several characterization curves show the TSV62x characteristics at 1.5 V. Additionally, the main specifications are guaranteed in extended temperature ranges from -40 °C to 125 °C.

3.2 Rail-to-rail input

The TSV62x is built with two complementary PMOS and NMOS input differential pairs. The device has a rail-to-rail input and the input common mode range is extended from $(V_{CC-}) - 0.1 \text{ V}$ to $(V_{CC+}) + 0.1 \text{ V}$. The transition between the two pairs appears at $V_{CC} - 0.7 \text{ V}$. In the transition region, the performances of CMRR, PSRR, V_{io} and THD are slightly degraded (as shown in *Figure 14* and *Figure 15* for V_{io} vs. V_{icm}).





The device is guaranteed without phase reversal.

3.3 Rail-to-rail output

The operational amplifier's output level can go close to the rails: 35 mV maximum above and below the rail when connected to a 10 k Ω resistive load to V_{CC}/2.



3.4 Shutdown function (TSV620)

The operational amplifier is enabled when the \overline{SHDN} pin is pulled high. To disable the amplifier, the \overline{SHDN} pin must be pulled down to $V_{\underline{CC}}$. When in shutdown mode, the amplifier output is in a high impedance state. The \overline{SHDN} pin must never be left floating but tied to $V_{\underline{CC}}$ or $V_{\underline{CC}}$.

The turn-on and turn-off times are calculated for an output variation of $\pm 200 \text{ mV}$ (*Figure 16* and *Figure 17* show the test configurations).





3.5 Optimization of DC and AC parameters

This device uses an innovative approach to reduce the spread of the main DC and AC parameters. An internal adjustment achieves a very narrow spread of current consumption (29 μ A typical, min/max at ±17 %). Parameters linked to the current consumption value, such as GBP, SR and AVd benefit from this narrow dispersion. All parts present a similar speed and the same behavior in terms of stability. In addition, the minimum values of GBP and SR are guaranteed (GBP = 350 kHz min, SR = 0.15 V/µs min).

3.6 Driving resistive and capacitive loads

These products are micro-power, low-voltage operational amplifiers optimized to drive rather large resistive loads, above 5 k Ω For lower resistive loads, the THD level may significantly increase.

In a *follower* configuration, these operational amplifiers can drive capacitive loads up to 100 pF with no oscillations. When driving larger capacitive loads, adding a small in-series resistor at the output can improve the stability of the device (see *Figure 20* for recommended in-series resistor values). Once the in-series resistor value has been selected, the stability of the circuit should be tested on bench and simulated with the simulation model.



Figure 20. In-series resistor vs. capacitive load

3.7 PCB layouts

For correct operation, it is advised to add 10 nF decoupling capacitors as close as possible to the power supply pins.



3.8 Macromodel

An accurate macromodel of the TSV620, TSV620A, TSV621, and TSV621A is available on STMicroelectronics' web site at www.st.com. This model is a trade-off between accuracy and complexity (that is, time simulation) of the TSV62x operational amplifiers. It emulates the nominal performances of a typical device within the specified operating conditions mentioned in the datasheet. It helps to validate a design approach and to select the right operational amplifier, *but it does not replace on-board measurements*.



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.



4.1 SOT23-5 package information



Figure 21. SOT23-5 package outline

Table 8. SOT23-5 mechanical data

	Dimensions								
Ref.		Millimeters		Inches					
	Min.	Тур.	Max.	Min.	Тур.	Max.			
А	0.90	1.20	1.45	0.035	0.047	0.057			
A1			0.15			0.006			
A2	0.90	1.05	1.30	0.035	0.041	0.051			
В	0.35	0.40	0.50	0.013	0.015	0.019			
С	0.09	0.15	0.20	0.003	0.006	0.008			
D	2.80	2.90	3.00	0.110	0.114	0.118			
D1		1.90			0.075				
е		0.95			0.037				
E	2.60	2.80	3.00	0.102	0.110	0.118			
F	1.50	1.60	1.75	0.059	0.063	0.069			
L	0.10	0.35	0.60	0.004	0.013	0.023			
К	0°		10°						



4.2 SOT23-6 package information





Table 9. SOT23-6 mechanical data

Dimensions							
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	0.90		1.45	0.035		0.057	
A1			0.10			0.004	
A2	0.90		1.30	0.035		0.051	
b	0.35		0.50	0.013		0.019	
с	0.09		0.20	0.003		0.008	
D	2.80		3.05	0.110		0.120	
E	1.50		1.75	0.060		0.069	
е		0.95			0.037		
Н	2.60		3.00	0.102		0.118	
L	0.10		0.60	0.004		0.024	
٥	0		10°				



4.3 SC70-5 (or SOT323-5) package information



Figure 23. SC70-5 (or SOT323-5) package outline

Table 10. SC70-5 (or SOT323-5) mechanical data

	Dimensions						
Ref	Millimeters			Inches			
	Min	Тур	Мах	Min	Тур	Max	
А	0.80		1.10	0.315		0.043	
A1			0.10			0.004	
A2	0.80	0.90	1.00	0.315	0.035	0.039	
b	0.15		0.30	0.006		0.012	
С	0.10		0.22	0.004		0.009	
D	1.80	2.00	2.20	0.071	0.079	0.087	
E	1.80	2.10	2.40	0.071	0.083	0.094	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65			0.025		
e1		1.30			0.051		
L	0.26	0.36	0.46	0.010	0.014	0.018	
<	0°		8°				



4.4 SC70-6 (or SOT323-6) package information



Figure 24. SC70-6 (or SOT323-6) package outline

Table 11. SC70-6 (or SOT323-6) mechanical data

	Dimensions						
Ref	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
А	0.80		1.10	0.031		0.043	
A1			0.10			0.004	
A2	0.80		1.00	0.031		0.039	
b	0.15		0.30	0.006		0.012	
С	0.10		0.18	0.004		0.007	
D	1.80		2.20	0.071		0.086	
Е	1.15		1.35	0.045		0.053	
е		0.65			0.026		
HE	1.80		2.40	0.071		0.094	
L	0.10		0.40	0.004		0.016	
Q1	0.10		0.40	0.004		0.016	





Figure 25. SC70-6 (or SOT323-6) recommended footprint



5 Ordering information

Part number	Temperature range	Package	Packing	Marking	
TSV620ILT	-40 °C to 125 °C	SOT23-6	Tape and reel	K107	
TSV620ICT		SC70-6		K14	
TSV620AILT		SOT23-6		K110	
TSV620AICT		SC70-6		K15	
TSV621ILT		SOT23-5		K106	
TSV621ICT		SC70-5		K16	
TSV621AILT		SOT23-5		K139	
TSV621AICT		SC70-5		K39	

Table 12. Order codes



6 Revision history

Date	Revision	Changes
12-Jan-2009	1	Initial release.
19-Oct-2009	2	Added TSV620 device (version with shutdown function). Added Table 4: Shutdown characteristics V_{CC} = 1.8 V. Added Table 7: Shutdown characteristics V_{CC} = 5 V. Added Section 3.4: Shutdown function (TSV620) on page 13. Added Section 4.2: SOT23-6 package mechanical data. Added Section 4.4: SC70-6 (or SOT323-6) package mechanical data. Added order codes in Table 12.
10-May-2017	3	Table 3, Table 5, and Table 6: changed "DVio to $\Delta V_{io}/\Delta T$, updated V_{OH} parameter information, changed min. values for V_{OH} parameterto max. values.Figure 21, Figure 22, Table 8, and Table 9: removed "L" from titles

Table 13. Document revision history



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